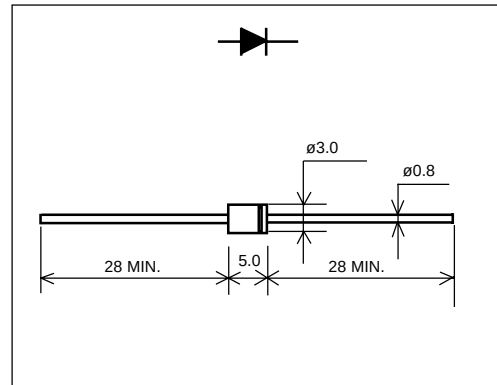


ERB37 (1.0A)

(800 to 1000V / 1.0A)

FAST RECOVERY DIODE

■ Outline drawings, mm



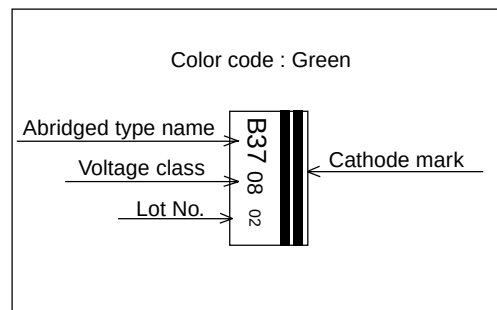
■ Features

- Super high speed switching
- Low V_F in turn on
- High reliability

■ Applications

- High speed switching

■ Marking



■ Maximum ratings and characteristics

- Absolute maximum ratings

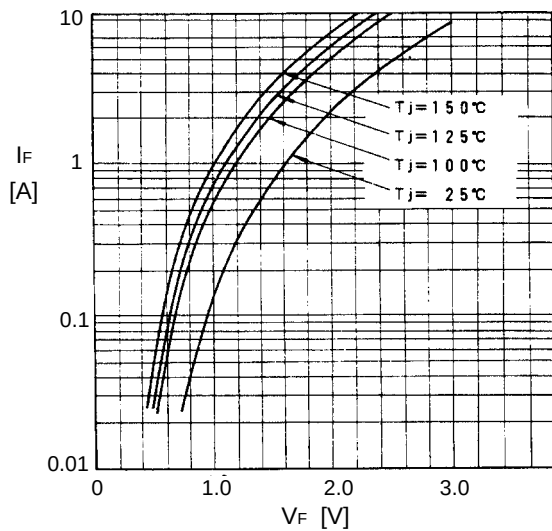
Item	Symbol	Conditions	Rating		Unit
			-08	-10	
Repetitive peak reverse voltage	V_{RRM}		800	1000	V
Non-repetitive peak reverse voltage	V_{RSM}		800	1000	V
Average forward current	$I_{F(AV)}$	Resistive load ($T_J = 125^\circ\text{C}$)	1.0		A
Surge current	I_{FSM}	Sine wave 10ms	30		A
Operating junction temperature	T_J		-40 to +150		$^\circ\text{C}$
Storage temperature	T_{stg}		-40 to +150		$^\circ\text{C}$

- Electrical characteristics ($T_a = 25^\circ\text{C}$ Unless otherwise specified)

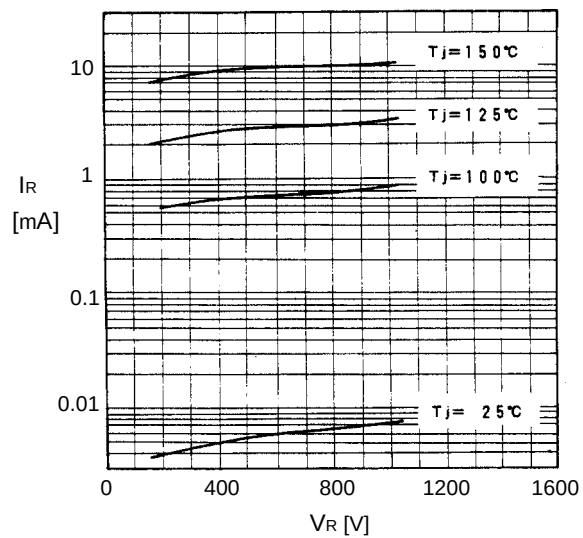
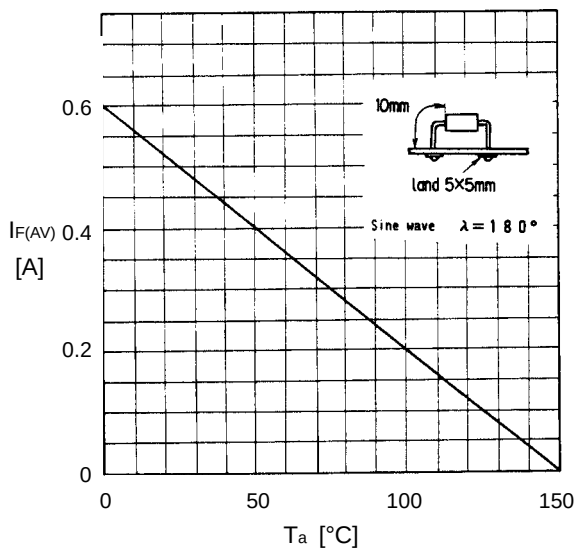
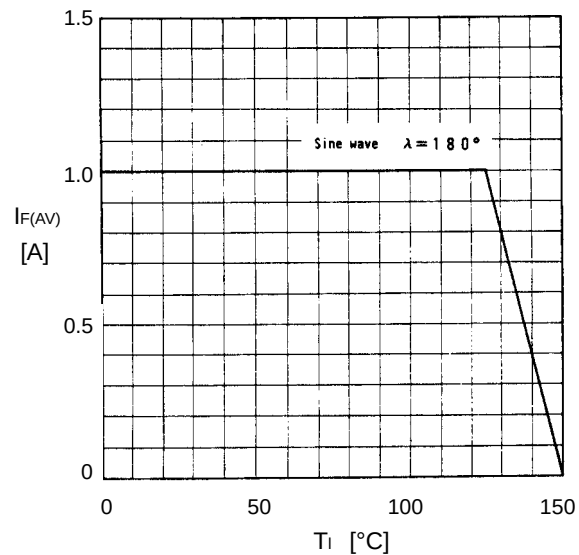
Item	Symbol	Conditions	Max.	Unit
Forward voltage drop	V_{FM}	$I_{FM} = 1.0\text{A}$	3.0	V
Reverse current	I_{RRM}	$V_R = V_{RRM}$	10	μA
Reverse recovery time	t_{rr}	$I_F = 0.1\text{A}$, $I_R = 0.1\text{A}$	250	ns

■ Characteristics

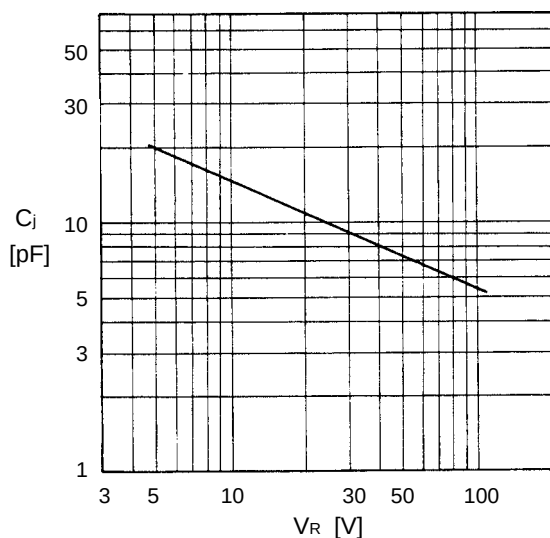
Forward characteristics



Reverse characteristics

Current derating ($I_{F(AV)}-T_a$)Current derating ($I_{F(AV)}-T_l$)

Junction capacitance characteristics



Surge capability

